High Reliability NPN Silicon Phototransistor



OP804, OP805 (TX, TXV)

Features:

- TO-18 hermetically sealed package
- · Lensed for high sensitivity
- Narrow acceptance angle
- Processed after MIL-PRF-19500
- Mechanically and spectrally matched to high reliability IREDs in the OP235 and OP236 series



Description:

Each device in this series consists of a high reliability NPN silicon phototransistor mounted in a hermetically sealed TO-18 package, which offers high power dissipation and superior hostile environment operation. Device lensing creates a 12° angle when measured from the optical axis to the half power point.

These devices can be matched with a solid state infrared source (such as the high resolution OP235 and OP236 series of IREDs), or can be used to sense infrared content in a visible light source (such as a tungsten bulb or sunlight) for automatic brightness control.

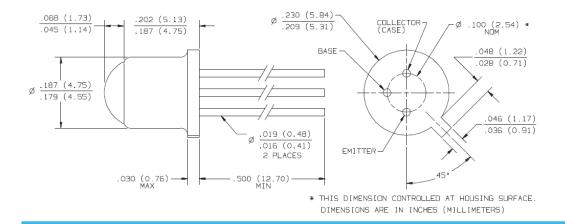
TX and TXV devices are processed to MIL-PRF-19500.

Please refer to Application Bulletins 208 and 210 for additional design information and reliability (degradation) data.

Applications:

- Space-limited applications
- Hostile environment applications

Part Number	Sensor	Light Current I _{C(ON)} (mA) Min / Max	V _{CE} Typ/Max	Input Power E _E (mW/cm ²)	Viewing Angle	Lead Length
OP804TX		7.00 / 22.00				
OP804TXV	Transistar	7.00 / 22.00	5	F 0	25°	0.50"
OP805TX	Transistor	15 00 / NIA) 3	5.0	25	0.50
OP805TXV		15.00 / NA				



General Note

TT Electronics | OPTEK Technology, Inc. 1645 Wallace Drive, Carrollton, TX 75006 | Ph: +1 972 323 2200 sensors@ttelectronics.com | www.ttelectronics.com

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Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Storage Temperature Range	-65° C to +150° C
Operating Temperature Range	-55° C to +125° C
Collector-Base Voltage	30 V
Collector-Emitter Voltage	30 V
Emitter-Base Voltage	5 V
Emitter-Collector Voltage (applies to all OP800 and OP830 devices)	5 V
Lead Soldering Temperature [1/16 inch (1.6mm) fro case for 5 seconds with soldering iron] (1)	260° C
Power Dissipation ⁽²⁾	250 mW

Electrical Characteristics (T_A = 25°C unless otherwise noted)

Input Diode

SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS
I _{C (ON)}	On-State Collector Current OP804 (TX, TXV OP805 (TX, TXV)	7.0 15.0		8 22	mA	$V_{CE} = 5.0V$, $E_e = 20 \text{ mW/cm}^{2(3)}$
I _{CEO} Collecto	Collector-Emitter Dark Current			100	nA	V _{CE} = 10.0 V, E _e = 0
	Conector-Emitter Dark Current			100	μΑ	$V_{CE} = 30.0 \text{ V}, E_e = 0 T_A = 100^{\circ} \text{ C}$
$V_{(BR)CEO}$	Collector-Base Breakdown Voltage	30			V	I_C = 100 μ A, I_B = 0, E_e = 0
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	7.0			V	I _C = 100 μA, E _e = 0
V _{CE(SAT)}	Collector-Emitter Saturation Voltage			0.40	V	$I_C = 0.4 \text{ mA, } E_e = 20 \text{ mW/cm}^{(2)(3)}$
t _f	Rise Time OP804 (TX, TXV) OP805 (TX, TXV)			10.0 15.0		V 20V L 100 mA BL 100 C
t _r	Fall Time OP804 (TX, TXV) OP805 (TX, TXV)			10.0 15.0	μs	$V_{cc} = 30 \text{ V}, I_c = 1.00 \text{ mA}, RL = 100 \Omega$

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (2) Derate linearly 2.5 mW/° C above 25° C.
- (3) Light source is an unfiltered tungsten lamp operated at a temperature of 2870 K

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